

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A light-emitting device ~~characterized by~~ comprising:
a pixel comprising:
 - a light-emitting element,
 - a first transistor for deciding a value of a current flowing to the light-emitting element, and
 - a second transistor for deciding a light emission or non light emission of the light-emitting element depending on a video signal,wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power unit and a third power unit, and
wherein a gate electrode of the first transistor is connected to a second power unit.
2. (Currently Amended) A light-emitting device ~~characterized by~~ comprising:
a pixel comprising:
 - a light-emitting element,
 - a first transistor for deciding a value of a current flowing to the light-emitting element,
 - a second transistor for deciding a light emission or non light emission of the light-emitting element depending on a video signal, and
 - a third transistor for controlling an input of the video signal,wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power unit and a third power unit, and
wherein a gate electrode of the first transistor is connected to a second power unit.
3. (Currently Amended) A light-emitting device ~~characterized by~~ comprising:

a pixel comprising:

a light-emitting element,

a first transistor for deciding a value of a current flowing to the light-emitting element,

a second transistor for deciding a light emission or non light emission of the light-emitting element depending on a video signal,

a third transistor for controlling an input of the video signal, and

a fourth transistor for forcing the light-emitting element into a non-emission state irrelevant from the video signal,

wherein the light-emitting element, the first transistor, and the second transistor are connected in series between a first power unit and a third power unit, and

wherein a gate electrode of the first transistor is connected to a second power unit.

4. (Currently Amended) The light-emitting device according to ~~any one of claims~~claim 1 to 3, characterized in that wherein the first transistor and the second transistor are identical in conductivity.

5. (Currently Amended) The light-emitting device according to ~~any one of claims~~claim 1 to 3, characterized in that wherein the first transistor ~~[[is of]]~~ comprises a depletion type.

6. (Currently Amended) The light-emitting device according to ~~any one of claims~~claim 1 to 3, characterized in that wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

7. (Currently Amended) The light-emitting device according to claim 6, ~~characterized in that~~ wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

8. (Currently Amended) An element substrate ~~characterized by~~ comprising:

a pixel comprising:

a pixel electrode;

a first transistor for deciding a value of a current flowing to the pixel electrode,

and

a second transistor for deciding a supply or non-supply of a current to the pixel electrode depending on a video signal,

wherein the first transistor and the second transistor are connected in series between a first power unit and the pixel electrode, and

wherein a gate electrode of the first transistor is connected to a second power unit.

9. (Currently Amended) The element substrate according to claim 8, ~~characterized in that~~ wherein each of the first transistor and the second transistor has a P-type conductivity, and a threshold value of the first transistor is higher than that of the second transistor.

10. (Currently Amended) The element substrate according to claim 8, ~~characterized in that~~ wherein each of the first transistor and the second transistor has an N-type conductivity, and a threshold value of the first transistor is lower than that of the second transistor.

11. (Currently Amended) The element substrate according to ~~any one of claims~~ claim 8 to 10, ~~characterized in that~~ wherein the first transistor ~~[[is of]]~~ comprises a depletion type.

12. (Currently Amended) The element substrate according to ~~any one of claims~~ claim 8 to 10, ~~characterized in that~~ wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

13. (Currently Amended) The element substrate according to claim 12, ~~characterized in that~~ wherein a ratio of the channel length to the channel width of the first transistor is 5 or more.

14. (New) The light-emitting device according to claim 2, wherein the first transistor and the second transistor are identical in conductivity.

15. (New) The light-emitting device according to claim 3, wherein the first transistor and the second transistor are identical in conductivity.

16. (New) The light-emitting device according to claim 2, wherein the first transistor comprises a depletion type.

17. (New) The light-emitting device according to claim 3, wherein the first transistor comprises a depletion type.

18. (New) The light-emitting device according to claim 2, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

19. (New) The light-emitting device according to claim 3, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

20. (New) The element substrate according to claim 9, wherein the first transistor comprises a depletion type.

21. (New) The element substrate according to claim 10, wherein the first transistor comprises a depletion type.

22. (New) The element substrate according to claim 9, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.

23. (New) The element substrate according to claim 10, wherein the first transistor has a channel length longer than a channel width, and the second transistor has a channel length equal to or shorter than a channel width.